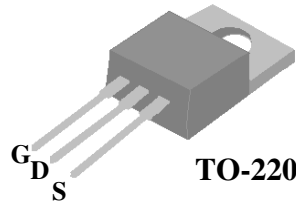




- ▼ Simple Drive Requirement
- ▼ Low On-resistance
- ▼ Fast Switching Characteristics

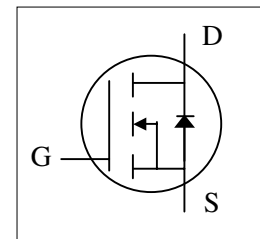


$BV_{DSS}$	900V
$R_{DS(ON)}$	7.2 $\Omega$
$I_D$	1.9A

**Description**

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is widely preferred for all commercial-industrial applications. The device is suited for DC-DC, AC-DC converters for power applications.



**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	900	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	1.9	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	1.2	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	6	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	62.5	W
	Linear Derating Factor	0.5	W/ $^\circ C$
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	18	mJ
$I_{AR}$	Avalanche Current	1.9	A
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

**Thermal Data**

Symbol	Parameter	Value	Units
$R_{thj-c}$	Maximum Thermal Resistance, Junction-case	2	$^\circ C/W$
$R_{thj-a}$	Maximum Thermal Resistance, Junction-ambient	62	$^\circ C/W$



# AP02N90P

## Electrical Characteristics@T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =1mA	900	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.8	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>3</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =0.85A	-	-	7.2	Ω
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	-	4	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =1.9A	-	2	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =900V, V <sub>GS</sub> =0V	-	-	10	uA
	Drain-Source Leakage Current (T <sub>j</sub> =125°C)	V <sub>DS</sub> =720V, V <sub>GS</sub> =0V	-	-	100	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>3</sup>	I <sub>D</sub> =1.9A	-	12	20	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =540V	-	2.5	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =10V	-	4.7	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>3</sup>	V <sub>DD</sub> =450V	-	10	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1.9A	-	5	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =10Ω, V <sub>GS</sub> =10V	-	18	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =236Ω	-	9	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	630	1000	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	40	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	4	-	pF

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>3</sup>	I <sub>S</sub> =1.9A, V <sub>GS</sub> =0V	-	-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time <sup>3</sup>	I <sub>S</sub> =1.9A, V <sub>GS</sub> =0V,	-	360	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs	-	1.8	-	μC

### Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Starting T<sub>j</sub>=25°C, V<sub>DD</sub>=50V, L=10mH, R<sub>G</sub>=25Ω, I<sub>AS</sub>=1.9A.
- 3.Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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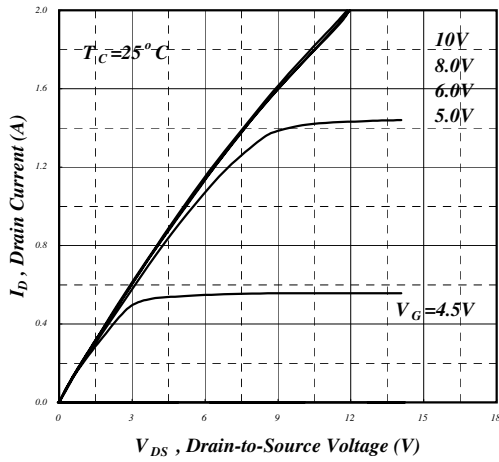


Fig 1. Typical Output Characteristics

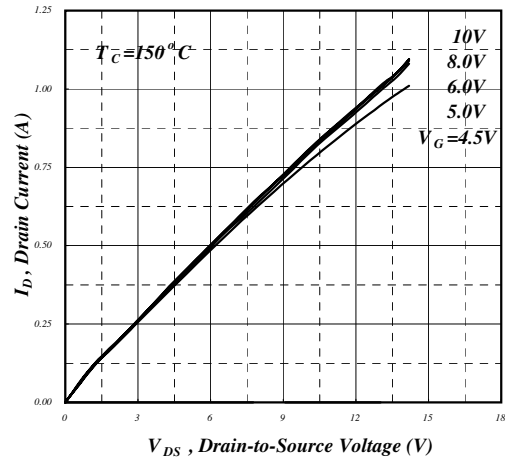


Fig 2. Typical Output Characteristics

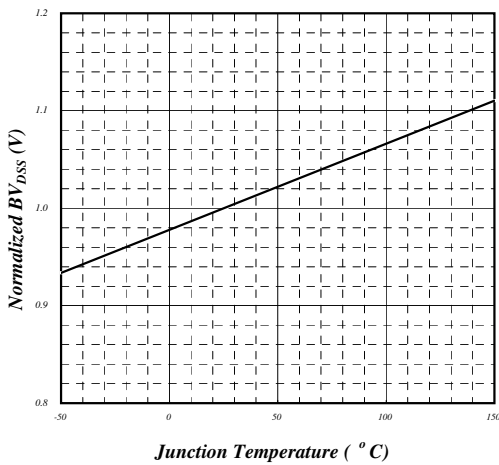


Fig 3. Normalized  $BV_{DSS}$  v.s. Junction Temperature

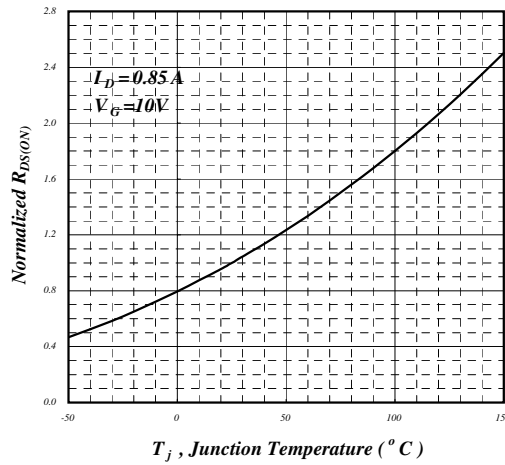


Fig 4. Normalized On-Resistance v.s. Junction Temperature

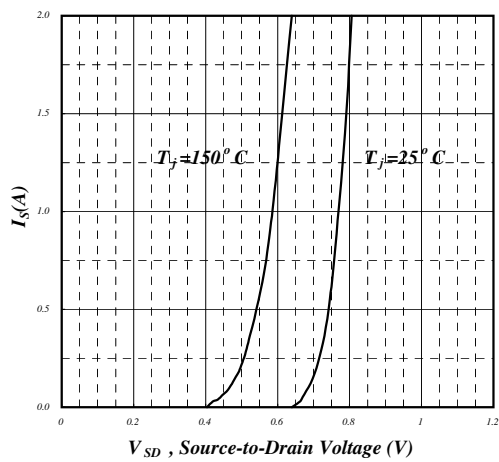


Fig 5. Forward Characteristic of Reverse Diode

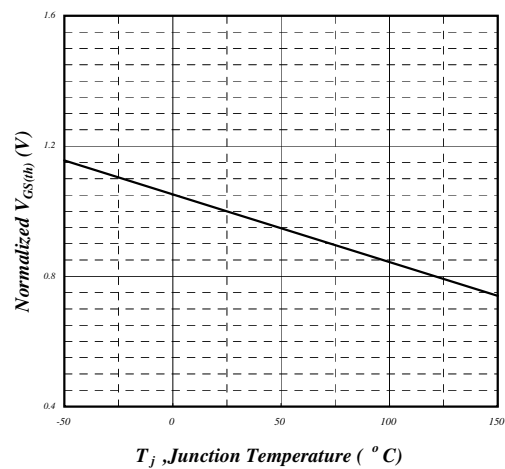


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

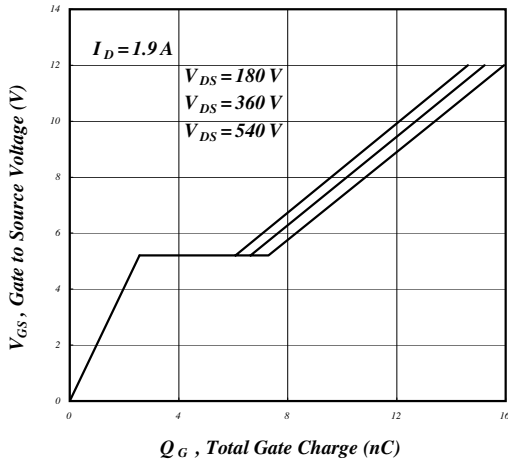


Fig 7. Gate Charge Characteristics

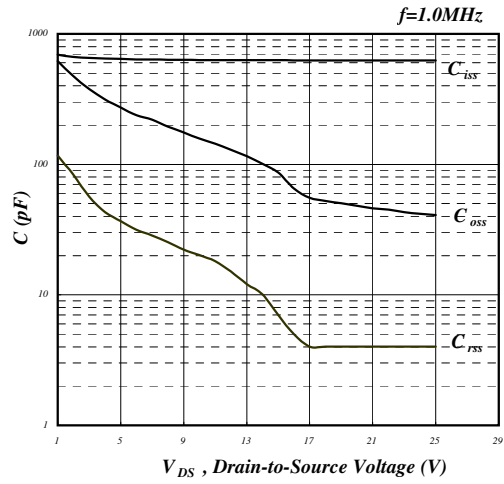


Fig 8. Typical Capacitance Characteristics

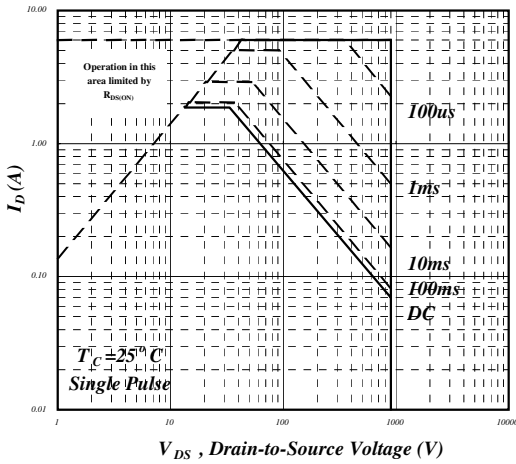


Fig 9. Maximum Safe Operating Area

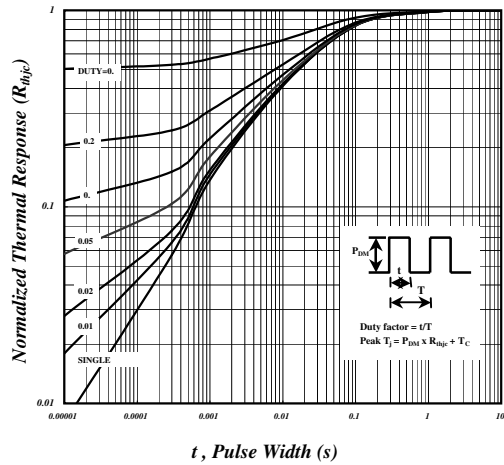


Fig 10. Effective Transient Thermal Impedance

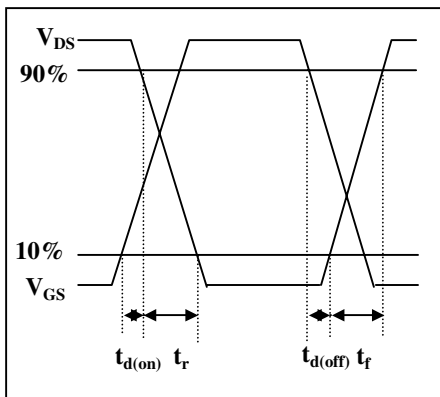


Fig 11. Switching Time Waveform

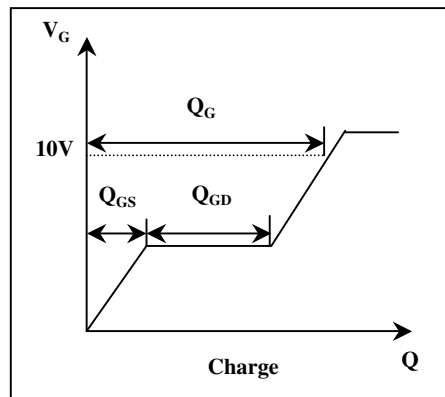


Fig 12. Gate Charge Waveform